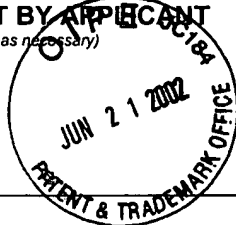


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Application Number	09/943134
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Unknown

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Attorney Docket No: 01303.020US1

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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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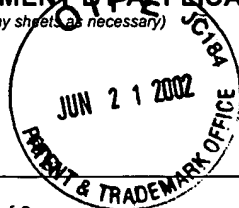
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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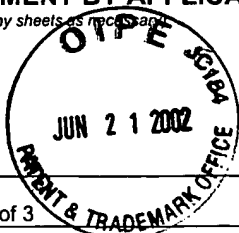
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Application Number	09/943134
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